

DATA SHEET

BS208

P-channel enhancement mode
vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995

P-channel enhancement mode vertical D-MOS transistor

BS208

FEATURES

- Direct interface to C-MOS
- High-speed switching
- No secondary breakdown.

DESCRIPTION

P-channel enhancement mode vertical D-MOS transistor in a TO-92 envelope. Intended for use in relay, high-speed and line transformer drivers.

PINNING - TO-92

PIN	DESCRIPTION
1	source
2	gate
3	drain

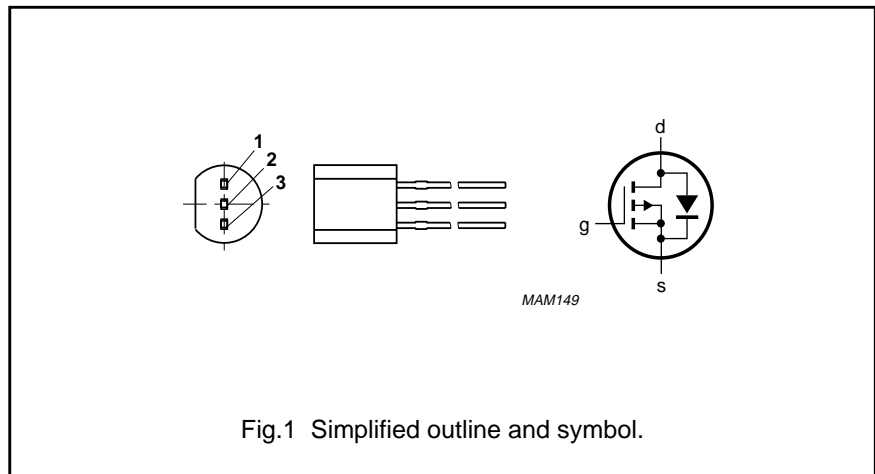


Fig.1 Simplified outline and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage (DC)		–	–	–200	V
V_{GSO}	gate-source voltage (DC)	open drain	–	–	± 20	V
$ Y_{fs} $	forward transfer admittance	$I_D = -200 \text{ mA}; V_{DS} = -25 \text{ V}$	100	200	–	mS
I_D	drain current (DC)		–	–	–0.2	A
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -200 \text{ mA}$	–	10	14	Ω
P_{tot}	total power dissipation	$T_{amb} = 25 \text{ }^\circ\text{C}$	–	–	0.83	W

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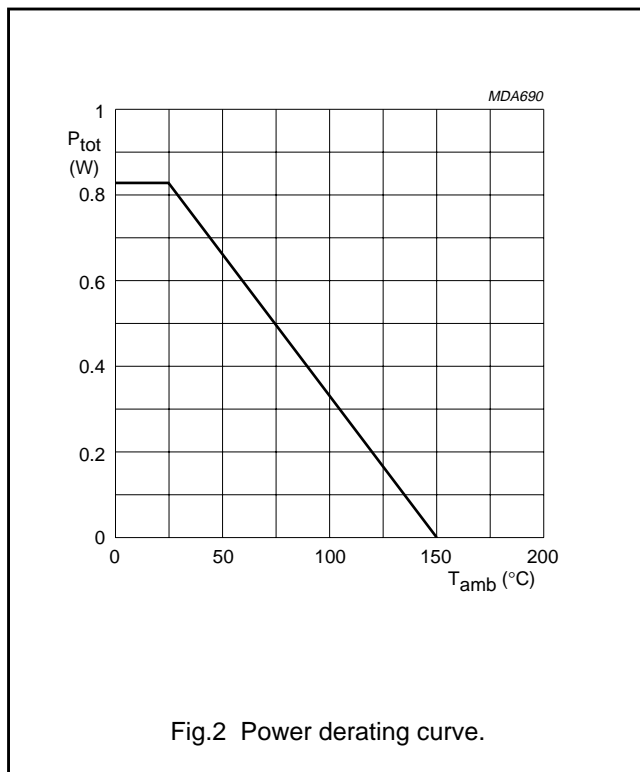
LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{DS}$	drain-source voltage		-	200	V
$\pm V_{GSO}$	gate-source voltage	open drain	-	20	V
$-I_D$	drain current	DC	-	0.2	A
$-I_{DM}$	drain current	peak value	-	0.6	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$	-	0.83	W
T_{stg}	storage temperature range		-65	+150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	MAX.	UNIT
R_{thj-a}	from junction to ambient	150	K/W



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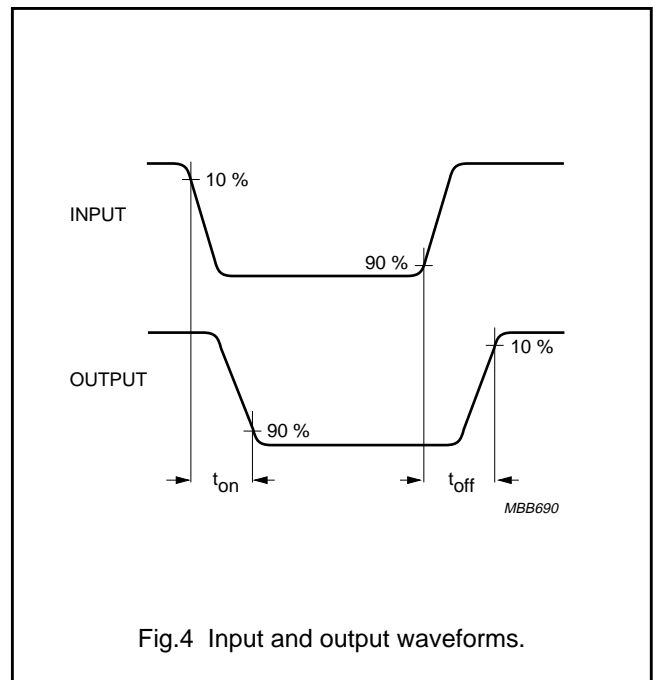
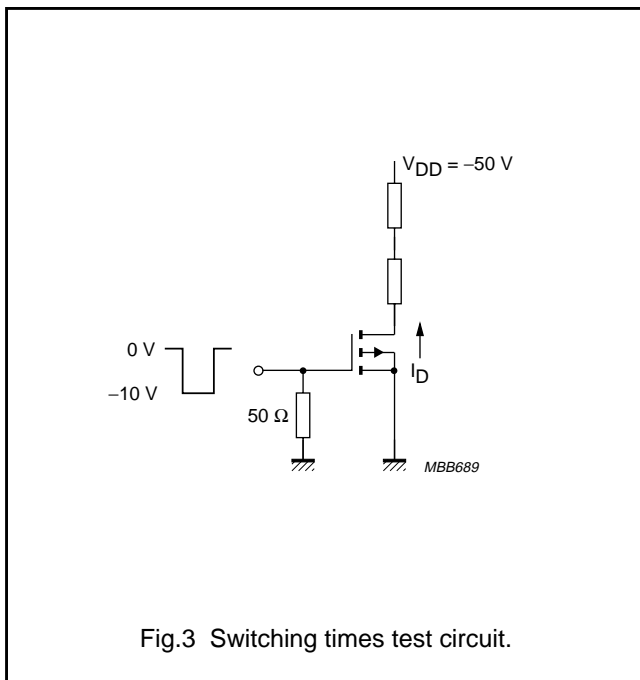
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
-V _{(BR)DSS}	drain-source breakdown voltage	-V _{GS} = 0 -I _D = 10 μA	200	-	-	V
-I _{DSS}	drain-source leakage current	-V _{DS} = 130 V V _{GS} = 0	-	-	1	μA
-I _{DSS}	drain-source leakage current	-V _{DS} = 70 V -V _{GS} = 0.2 V	-	-	25	μA
-I _{GSS}	gate-source leakage current	-V _{GS} = 20 V V _{DS} = 0	-	-	100	nA
-V _{GS(th)}	gate-source threshold voltage	V _{GS} = V _{DS} -I _D = 1 mA	0.8	-	2.8	V
R _{DS(on)}	drain-source on-resistance	-V _{GS} = 10 V -I _D = 200 mA	-	-	14	Ω
Y _{fs}	transfer admittance	-V _{DS} = 25 V -I _D = 200 mA	100	200	-	mS
C _{iss}	input capacitances	note 1	-	55	90	pF
C _{oss}	output capacitance	note 1	-	20	30	pF
C _{rss}	feedback capacitance	note 1	-	5	15	pF
t _{on}	turn-on time	note 2	-	5	10	ns
t _{off}	turn-off time	note 2	-	20	30	ns

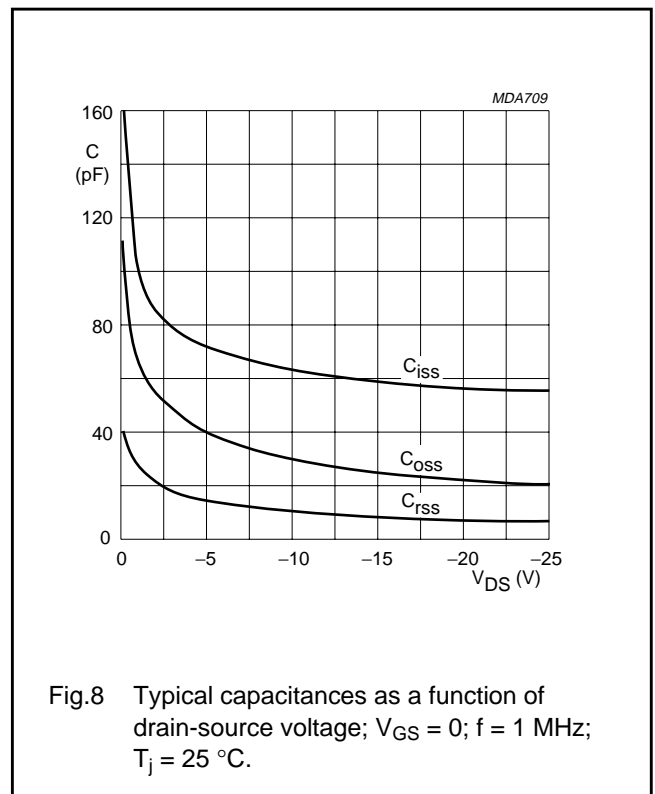
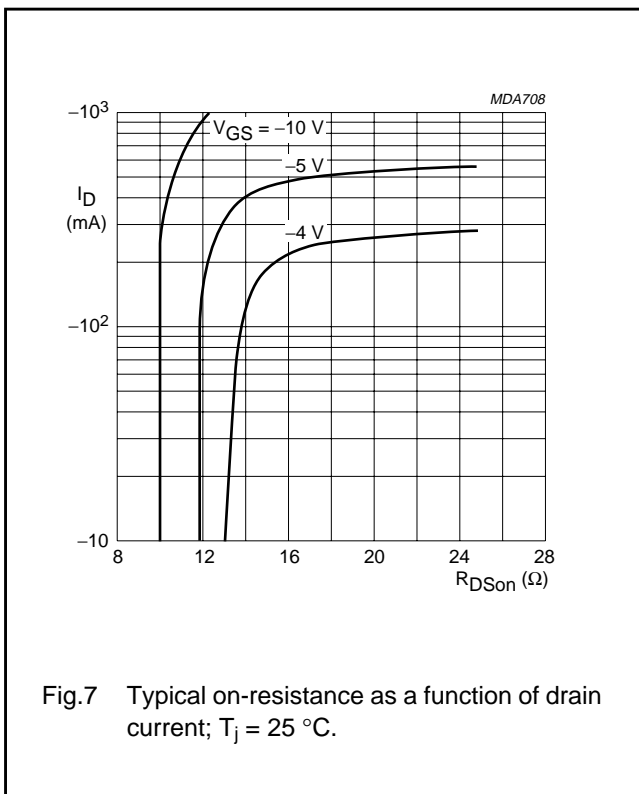
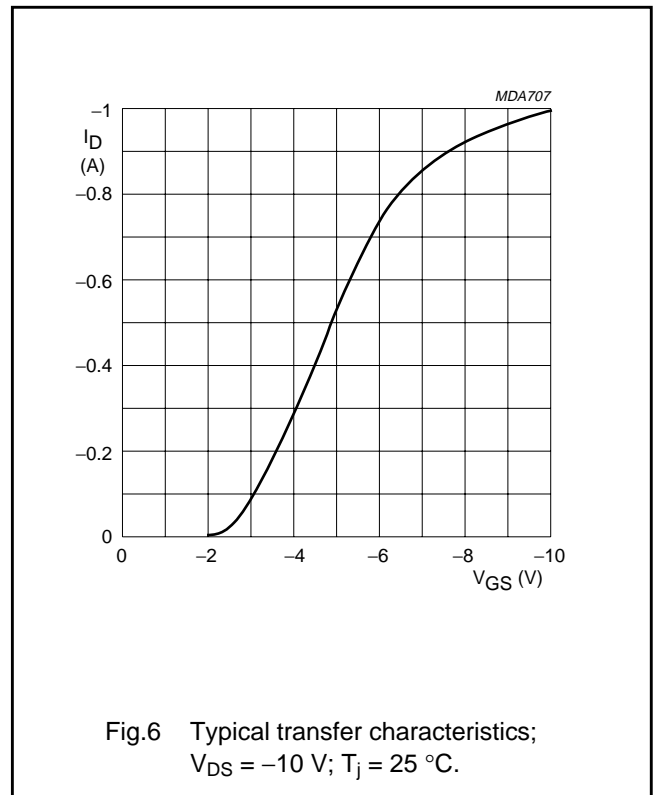
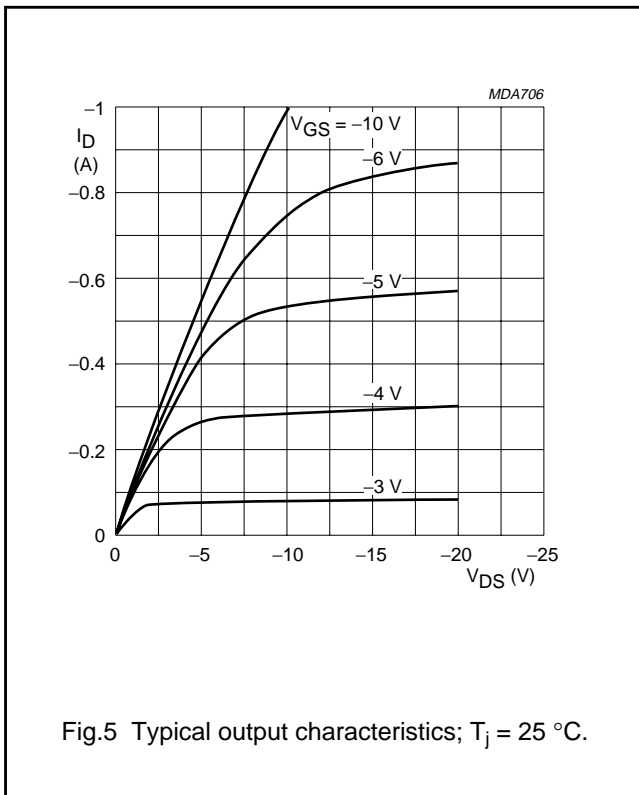
Notes

1. Measured at f = 1 MHz; -V_{DS} = 25 V; V_{GS} = 0.
2. -V_{GS} = 0 to 10 V; -I_D = 250 mA; -V_{DD} = 50 V.



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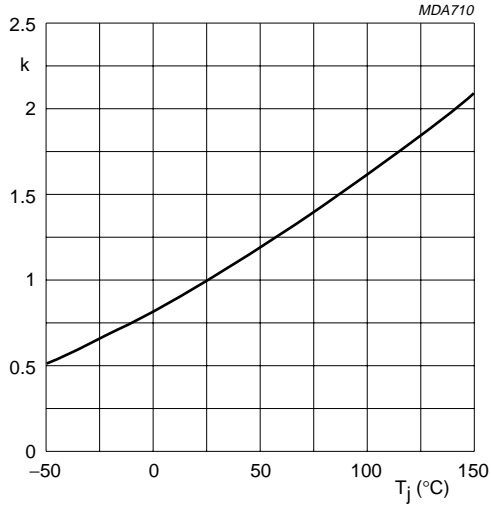


Fig.9 Temperature coefficient of drain-source on-resistance;

$$k = \frac{R_{DS(on)} \text{ at } T_j}{R_{DS(on)} \text{ at } 25^\circ\text{C}};$$

typical R_{DS(on)} at 200 mA/10 V.

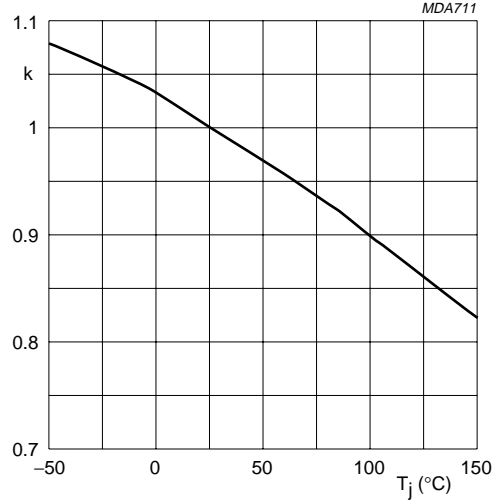


Fig.10 Temperature coefficient of gate-source threshold voltage;

$$k = \frac{V_{GS(th)} \text{ at } T_j}{V_{GS(th)} \text{ at } 25^\circ\text{C}};$$

typical V_{GS(th)} at 1 mA.

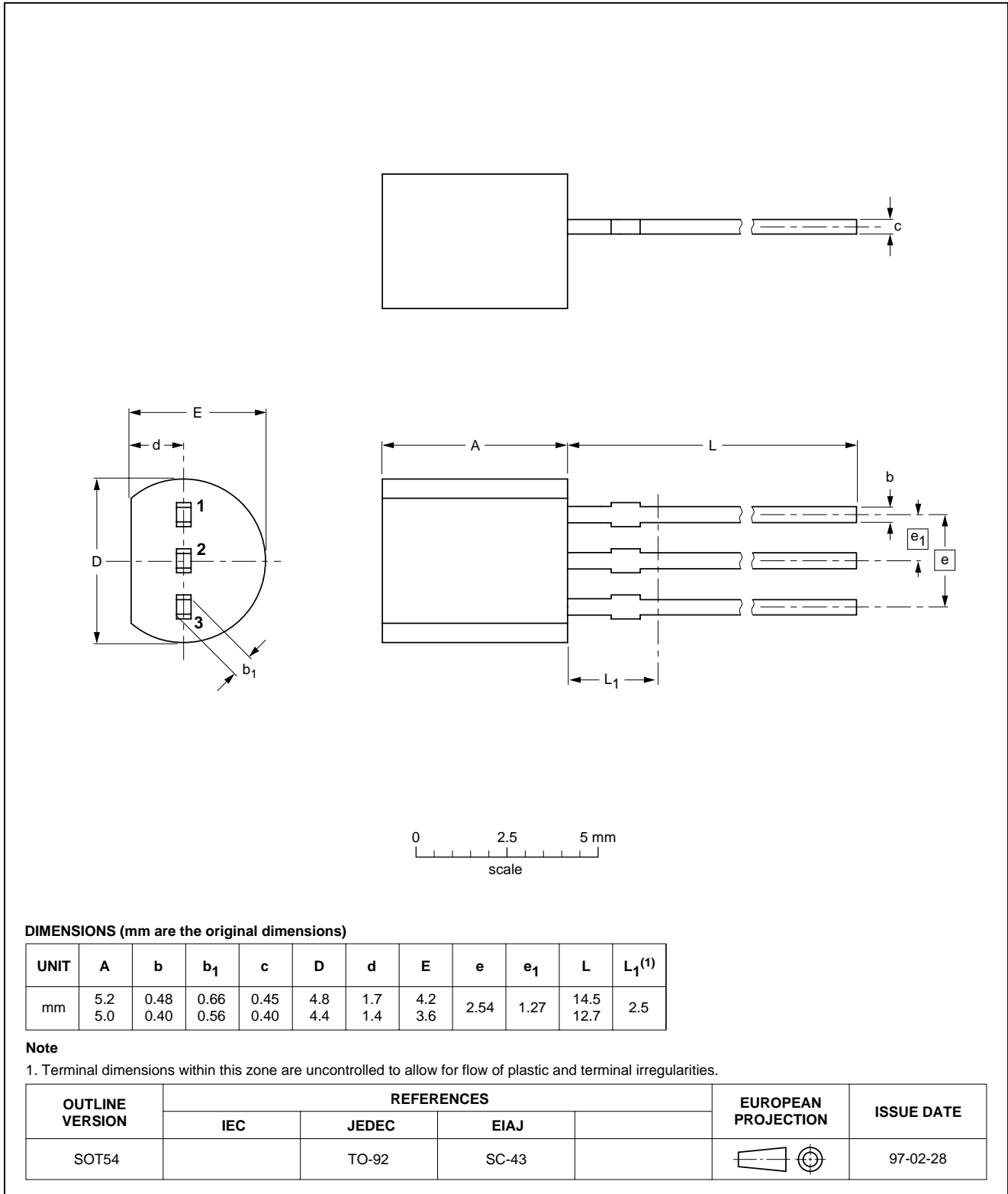
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PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



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BS208**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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